AMENDMENTS TO THE CLAIMS

This listing of claims replaces all prior versions of claims in the application.

1. (Currently Amended): A semiconductor device fabrication method comprising:

a first polishing of polishing a surface of a film-to-be-polished ~~formed over a semiconductor substrate with a polishing pad~~ while ~~only~~ a polishing slurry including abrasive grains and a surfactant is supplied onto [[the]] a polishing pad ~~to planarize the surface of the film-to-be-polished~~ through a first nozzle; and

~~after the surface of the film-to-be-polished has been planarized, further~~ a second polishing of polishing the surface of the film-to-be-polished ~~with a polishing pad~~ while said polishing slurry is supplied onto a polishing pad through the first nozzle and water [[are]] is further supplied onto the polishing pad through a second nozzle different from the first nozzle, ~~said polishing slurry and said water being supplied onto the polishing pad separately,~~

~~wherein said polishing slurry comprises abrasive grains and a surfactant additive, and~~

wherein ~~in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle~~ supply of said water through the second nozzle starts at the second polishing after the first polishing.

2 (Cancelled).

3. (Currently Amended): A semiconductor device fabrication method ~~comprising:~~ according to claim 1, wherein

~~polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to planarize the surface of the film-to-be-polished; and~~

~~after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,~~

~~wherein said polishing slurry comprises abrasive grains and a surfactant additive,~~

~~wherein~~ in the ~~further~~ second polishing ~~the surface of the film-to-be-polished~~, [[the]] said water is supplied to a position outer of a position for said polishing slurry to be supplied to~~, and~~

~~wherein in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle~~.

4. (Currently Amended): A semiconductor device fabrication method ~~comprising:~~ according to claim 1, wherein

~~polishing a surface of a film-to-be-polished formed over a semiconductor substrate with a polishing pad while only a polishing slurry is supplied onto the polishing pad to planarize the surface of the film-to-be-polished; and~~

~~after the surface of the film-to-be-polished has been planarized, further polishing the surface of the film-to-be-polished with a polishing pad while said polishing slurry and water are supplied onto the polishing pad, said polishing slurry and said water being supplied onto the polishing pad separately,~~

~~wherein said polishing slurry comprises abrasive grains and a surfactant additive,~~

~~wherein~~ in the ~~further~~ second polishing ~~the surface of the film-to-be-polished~~, a supply amount of said water is 2 or more times as much as a supply amount of said polishing slurry~~, and~~

~~wherein in the further polishing the surface of the film-to-be-polished, said polishing slurry is supplied onto the polishing pad through a nozzle, and said water is supplied onto the polishing pad through another nozzle~~.

5-11 (Cancelled).

12. (Currently Amended): A semiconductor device fabrication method according to claim 1, further comprising, before the ~~planarizing the surface of the film-to-be-polished~~ first polishing:

forming over [[the]] a semiconductor substrate an insulation film having polish characteristics different from those of the film-to-be-polished;

forming an opening in the insulation film;

etching the semiconductor substrate with the insulation film as a mask to form a trench in the semiconductor substrate; and

forming the film-to-be-polished in the trench and over the insulation film,

in the ~~further~~ second polishing ~~the surface of the film-to-be-polished~~, the surface of the film-to-be-polished is polished with the insulation film as a stopper.

13-27 (Cancelled).

28. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

the abrasive grains comprise cerium oxide or silicon oxide,

the ~~additive~~ surfactant comprises poly(ammonium acrylate).

29-33 (Cancelled)

34. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

in the ~~further~~ second polishing ~~the surface of the film-to-be-polished~~, a supply amount of said polishing slurry to a supply amount of said water is 1:5.

35. (Currently Amended): A semiconductor device fabrication method according to claim 1, wherein

the polishing pad used in the ~~further~~ second polishing ~~the surface of the film-to-be-polished~~ is different from the polishing pad used in the first polishing ~~the surface of the film-to-be-polished to planarize the surface of the film-to-be-polished~~.

36 (Cancelled).